

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (currently amended): A plasma immersion ion implantation reactor for ion implanting a species into a layer of a workpiece, comprising:

an enclosure comprising a side wall and a ceiling and defining a chamber;

a workpiece support pedestal within the chamber having a workpiece support surface facing said ceiling and defining a process region extending generally across said wafer support pedestal and confined laterally by said side wall and axially between said workpiece support pedestal and said ceiling;

said enclosure having ~~at least a first and second pair~~ pairs of openings at generally opposite sides of said process region, said first and second pairs being oriented transverse to one another, each pair of openings being separated from one another by a distance approximately equal to the diameter of said workpiece support, whereby the two openings of each pair are adjacent respective points along said side wall that are 180 degrees apart along the circumference of said side wall;

~~a first and second mutually transverse hollow conduit~~ conduits outside of said chamber, each conduit having first and second ends connected to respective openings ~~ones of said first~~ the corresponding pair of openings, so as to provide a first and second mutually transverse reentrant path paths extending through

said conduit and across said process region and intersecting one another in said process region;

gas distribution apparatus on or near an interior surface of said reactor for introducing a process gas containing the species to be ion implanted;

a first and second RF plasma source power applicator  
applicators for generating a plasma in said chamber adjacent said  
first and second conduits, respectively.

Claim 2 (original): The reactor of Claim 1 wherein said enclosure further comprises a base, and said interior surface of said reactor comprises one of: (a) said ceiling, (b) said side wall, (c) said conduit, (d) said base.

Claim 3 (original): The reactor of Claim 1 further comprising a pumping annular volume defined between said workpiece support pedestal and said side wall, and a vacuum pump coupled to said pumping annular volume.

Claim 4 (original): The reactor of Claim 1 wherein said first RF source power applicator is positioned to couple RF plasma source power into a region of said first hollow conduit.

Claim 5 (original): The reactor of Claim 1 wherein said plasma comprises a plasma current in said reentrant path that oscillates at an RF frequency of said first RF plasma source power applicator.

Claim 6 (previously presented): The reactor of Claim 1 wherein said first hollow conduit comprises a metal material, said reactor further comprising:

an annular insulating gap in said first hollow conduit

separating said first hollow conduit into axial sections.

Claim 7 (currently amended): The reactor of Claim ~~5~~ 6 wherein said ceiling comprises a constriction of said reentrant torroidal path in said process zone for enhancement of plasma ion density of said plasma current in said process zone.

Claim 8 (previously presented): The reactor of Claim 5 wherein said ceiling and said wafer support pedestal are separated by a gap therebetween, said gap being sufficiently small so that plasma ion density of said plasma current is greater in the vicinity of said workpiece support pedestal than elsewhere along said reentrant path.

Claim 9 (previously presented): The reactor of Claim 1 wherein the workpiece support pedestal comprises an electrostatic chuck, said electrostatic chuck comprising thermal control apparatus for workpiece temperature control.

Claim 10 (original): The reactor of Claim 9 further comprising a bias RF power generator coupled to said workpiece support pedestal to control a sheath voltage across a plasma sheath overlying said workpiece support pedestal.

Claim 11 (original): The reactor of Claim 9 further comprising a bias RF voltage generator coupled to said workpiece support pedestal to control a sheath voltage across a plasma sheath overlying said workpiece support pedestal.

Claim 12 (original): The reactor of Claim 1 further comprising a gas supply containing said process gas.

Claim 13 (original): The reactor of Claim 12 wherein said species to be implanted comprises a first atomic element, said process gas further comprising:

a second atomic element in chemical combination with said first atomic element.

Claim 14 (previously presented): The reactor of Claim 13 wherein said layer of said workpiece is a semiconductor material and said first atomic element is an n-type or p-type conductivity dopant impurity with respect to said semiconductor material.

Claim 15 (original): The reactor of Claim 14 wherein said second atomic element comprises a semiconductor element.

Claim 16 (previously presented): The reactor of Claim 15 wherein said second atomic element and said semiconductor material of said layer are the same atomic element.

Claim 17 (previously presented): The reactor of Claim 14 wherein said second atomic element is an element having a greater tendency than said first atomic element following ion implantation to diffuse out of said layer upon heating of said layer.

Claim 18 (original): The reactor of Claim 14 wherein said second atomic element comprises one of hydrogen and fluorine.

Claim 19 (original): The reactor of Claim 14 wherein the chemical combination of said first and second atomic species comprises a first molecular species, said process gas further comprising a second molecular species.

Claim 20 (original): The reactor of Claim 19 wherein said second molecular species comprises one of: (a) hydrogen-containing gas, (b) fluorine-containing gas.

Claim 21 (original): The reactor of Claim 19 wherein said second molecular species comprises a diluent gas.

Claim 22 (original): The reactor of Claim 21 wherein said first molecular species comprises a fluoride of said dopant impurity and said second molecular species comprises a hydride of said dopant impurity.

Claim 23 (original): The reactor of Claim 22 wherein said process gas further comprises a third molecular species.

Claim 24 (original): The reactor of Claim 23 wherein said third molecular species comprises a diluent gas.

Claim 25 (original): The reactor of Claim 23 wherein said third molecular species comprises at least one of (a) hydrogen-containing gas, (b) fluorine-containing gas, (c) an inert gas.

Claim 26 (cancelled)

Claim 27 (currently amended): The reactor of Claim ~~26~~ 1 further comprising one or more RF power source for furnishing RF power to said first and second RF power applicators.

Claim 28 (original): The reactor of Claim 27 wherein said RF power source furnishes RF power to said first and second RF power applicators at respective RF frequencies offset from one another.

Claim 29 (cancelled)

Claim 30 (currently amended): The reactor of Claim ~~29~~ 1 wherein said first and second paths are generally orthogonal to one another.

Claim 31 (currently amended): The reactor of Claim ~~6~~ 7 wherein said gas distribution apparatus comprises a gas distribution plate on said ceiling, said gas distribution plate being located in a region of said ceiling that is radially inward of said first and second pairs of openings, whereby said gas distribution plate is surrounded by said each of said reentrant paths and forms a boundary of the portion of each reentrant path lying within said process region.

Claim 32 (currently amended): The reactor of Claim ~~4~~ 31 wherein each opening of said pairs of openings is through said ceiling and is in a radially outward zone relative to said gas distribution plate, said gas distribution plate comprising plural gas injection orifices ~~said gas distribution apparatus comprises a gas distribution ring on said wall.~~

Claim 33 (original): The reactor of Claim 1 wherein said enclosure further comprises a base, and said gas distribution apparatus comprises a plurality of discrete gas injection nozzles or diffusers on one of: (a) said side wall, (b) said ceiling, (c) base of said chamber.

Claim 34 (currently amended): The reactor of Claim ~~26~~ 1 wherein said first and second RF power applicators comprise respective conductors coiled around respective ones of said first

and second hollow conduits, said respective conductors being coupled to respective ones of said first and second RF power sources.

Claim 35 (currently amended): The reactor of Claim [26] 1 wherein said ports are in said ceiling, whereby said hollow conduits terminate axially into said ports.

Claim 36 (withdrawn): The reactor of Claim 26 wherein said ports are in said side wall, whereby said hollow conduits terminate radially into said ports.

Claim 37 (withdrawn): The reactor of claim 26 wherein said ports are in said base of said chamber, whereby said hollow conduits terminate axially into said ports.

Claim 38 (original): The reactor of Claim 1 further comprising a bias power generator coupled to said workpiece support pedestal to control a sheath voltage across a plasma sheath overlying said workpiece support pedestal.

Claim 39 (original): The reactor of Claim 1 further comprising a bias voltage generator coupled to said workpiece support pedestal to control a sheath voltage across a plasma sheath overlying said workpiece support pedestal.

Claim 40 (original): The reactor of Claim 38 wherein said bias power generator has an RF bias frequency sufficiently low to enable ions traversing the plasma sheath to attain an energy corresponding to a peak-to-peak voltage of said bias power generator.

Claim 41 (original): The reactor of Claim 38 wherein said bias power generator has an RF frequency sufficiently high to limit RF voltage drops across dielectric layers on said workpiece support pedestal to less than a predetermined fraction of plasma sheath voltage near said workpiece support.

Claim 42 (original): The reactor of Claim 41 wherein said predetermined fraction corresponds to about 10%.

Claim 43 (currently amended): The reactor of Claim 28 wherein said offset frequencies are centered around ~~10 MHz~~ 13.56 MHz and are offset by about 200 kHz.

Claim 44 (currently amended): The reactor of Claim ~~26~~ 1 wherein said first and second hollow conduits are non-intersecting whereby said first and second paths intersect one another only in said process region.

Claim 45 (original): The reactor of Claim 1 wherein said gas distribution apparatus is in said ceiling and comprises a center orifice and plural outer orifices in a circle centered on said center orifice, said reactor further comprising:

a gas panel containing a separate gas supplies for respective process gases for doping and for passivating and for removing; and

a gas distribution controller comprising a first set of valves coupling at least one of said separate gas supplies to said center orifice and a second set of valves coupling at least some of said separate gas supplies to said plural outer orifices.

Claim 46 (original): The reactor of Claim 1 wherein said gas distribution apparatus comprises first and second sets of



plural orifices, said reactor further comprising:

a gas panel containing a separate gas supplies for respective process gases for doping and for passivating and for removing; and

a gas distribution controller comprising a first set of valves coupling at least one of said separate gas supplies to said first set of plural orifices and a second set of valves coupling at least some of said separate gas supplies to said second set of plural orifices.

Claim 47 (original): The reactor of Claim 45 wherein:

said gases for doping comprise a fluoride of a dopant species and a hydride of a dopant species,

said gases for passivating comprise a hydride of a passivating species and a fluoride of a passivating species,

said gases for removing comprise an etchant-containing gas and an inert gas; and

said gases for oxidizing comprise oxygen.

Claim 48 (original): The reactor of Claim 46 wherein:

said gases for doping comprise a fluoride of a dopant species and a hydride of a dopant species,

said gases for passivating comprise a hydride of a passivating species and a fluoride of a passivating species,

said gases for removing comprise an etchant-containing gas and an inert gas; and

said gases for oxidizing comprise oxygen.

Claim 49 (original): The reactor of Claim 47 wherein said gas distribution controller furnishes oxygen exclusively to said center orifice.

Claim 50 (original): The reactor of Claim 48 wherein said gas distribution controller furnishes oxygen exclusively to said second set of plural orifices.

Claim 51 (withdrawn): The reactor of Claim 38 further comprising a controller for controlling said bias power generator to produce a desired bias voltage at said workpiece support pedestal for a predetermined single burst duration.

Claim 52 (withdrawn): The reactor of Claim 51 wherein said controller comprises:

- a timer for switching the output of said bias power generator on and off in accordance with said predetermined duration;

- a peak voltage detector coupled to said workpiece support pedestal;

- a threshold comparator connected to said timer for comparing the output of said peak voltage detector with a predetermined threshold voltage;

- a subtractor having a pair of inputs connected to the output of said peak voltage detector and to a predetermined target voltage, respectively, and a feedback conditioner for processing the output of said subtractor;

- a first switch for coupling an output of said feedback conditioner to a power level control input of said bias power generator;

Claim 53 (withdrawn): The reactor of Claim 52 wherein said controller further comprises a control element for controlling said bias power generator (a) empirically in absence of a plasma in said chamber and (b) in a feedback control loop in the presence of plasma in said chamber.

Claim 54 (withdrawn): The reactor of Claim 53 wherein said control element comprises:

a voltage-to-power look-up table having an input connected to said predetermined target voltage and an output;

a second switch coupled between the output of said voltage-to-power look-up table and said power level control input of said bias power generator; and

a plasma detector in said chamber connected to control said first and second switches in complementary fashion in response to detection of plasma in said chamber.

Claim 55 (withdrawn): The reactor of Claim 54 wherein said plasma detector is further connected to enable said timer.

Claim 56 (withdrawn): The reactor of Claim 52 wherein said feedback conditioner is an integral proportional controller.

Claim 57 (withdrawn): The reactor of Claim 52 wherein said predetermined threshold voltage and said predetermined target voltage are identical.

Claim 58 (withdrawn): The reactor of Claim 52 further comprising a process controller for furnishing said predetermined target voltage and said predetermined threshold voltage.

Claim 59 (withdrawn): The reactor of Claim 1 further comprising a vacuum pump and a vacuum control valve coupling said vacuum pump to said chamber, said vacuum control valve comprising:

a valve housing having a valve opening defined by an

opening side wall having a surface parallel to an axis of said valve opening;

a rotatable flap subject to process control and having an area conformal with said valve opening and side wall and rotatably mounted within said valve opening to define a gap therebetween; and

a plurality of small indentational voids in said side wall that are covered by said rotatable flap whenever said flap is in a co-planar relationship with said housing and are gradually exposed as said flap rotates away from said rotational position and before a bottom corner edge of said flap passes a top surface of said valve housing.

Claim 60 (withdrawn): The reactor of Claim 1 wherein said workpiece support pedestal comprises:

a conductive wafer support plate;

a grounded conductive base plate forming at least a void between said support and base plates;

a side wall around said support and base plates forming at least a void between said side wall and said support and base plates;

a high dielectric filler material having a high breakdown voltage filling said voids; and

a conductive insert coupled to said bias power generator and a conductive female receptacle for tightly receiving said conductive insert, said conductive female receptacle being connected to said conductive wafer support plate, said conductive insert and said conductive female receptacle extending through said conductive base plate to said conductive wafer support plate, and insulating layer insulating said conductive insert from said conductive base plate.

Claim 61 (withdrawn): The reactor of Claim 60 wherein said workpiece support pedestal further comprises at least one lift pin assembly extending through said conductive base plate and said conductive wafer support plate and a axial void between said lift pin assembly and said lift pin assembly, and a high dielectric filler material having a high breakdown voltage within the void between said lift pin assembly and said conductive wafer support plate.

Claim 62 (withdrawn): The reactor of Claim 61 further comprising a fastening bolt extending at least partially through said conductive wafer support plate and to said conductive base plate, and a high dielectric filler material having a high breakdown voltage surrounding a portion of said bolt within said conductive wafer support plate.

Claim 63 (original): The apparatus of Claim 1 further comprising an RF source power generator coupled to said first RF power applicator and an RF bias power generator coupled to said workpiece support pedestal.

Claim 64 (withdrawn): The apparatus of Claim 63 wherein said RF source power generator and said RF bias power generator comprise first and second pulsed RF supplies, respectively.

Claim 65 (withdrawn): The apparatus of Claim 64 wherein said first and second pulsed RF supplies are in a push-pull relationship.

Claim 66 (withdrawn): The apparatus of Claim 64 wherein said first and second pulsed RF supplies are in an in-synchronism relationship.

Claim 67 (withdrawn): The apparatus of Claim 64 wherein said first and second RF supplies are in a symmetric relationship.

Claim 68 (withdrawn): The apparatus of Claim 64 wherein said first and second RF supplies are in a non-symmetric relationship.

Claim 69 (withdrawn): The apparatus of Claim 1 further comprising:

an RF source power generator connected to said first RF power applicator;

a D.C. bias power generator connected to said wafer support pedestal.

Claim 70 (withdrawn): The apparatus of Claim 69 wherein:

said RF source power generator and said D.C. bias power generator supply comprise first and second pulsed power supplies.

Claim 71 (withdrawn): The apparatus of Claim 70 wherein said first and second pulsed power supplies are in a push-pull relationship.

Claim 72 (withdrawn): The apparatus of Claim 70 wherein said first and second pulsed power supplies are in an in-synchronism relationship.

Claim 73 (withdrawn): The apparatus of Claim 70 wherein said first and second pulsed power supplies are in a symmetrical relationship.

Claim 74 (withdrawn): The apparatus of Claim 70 wherein said first and second pulsed power supplies are in a non-symmetrical relationship.

Claim 75 (original): The apparatus of Claim 38 wherein said bias power generator has a bias frequency that is sufficiently low for ions in a plasma sheath near said workpiece to follow electric field oscillations across said sheath at said bias frequency.

Claim 76 (original): The apparatus of Claim 75 wherein said bias frequency is sufficiently high so that RF voltage drops across dielectric layers on said workpiece do not exceed a predetermined fraction of the RF bias voltage applied to said workpiece support.

Claim 77 (original): The apparatus of Claim 76 wherein said predetermined fraction corresponds to about 10%.

Claim 78 (original): The apparatus of Claim 38 wherein said bias power generator has a bias frequency between 10 kHz and 10 MHz.

Claim 79 (original): The apparatus of Claim 38 wherein said bias power generator has a bias frequency between 50 kHz and 5 MHz.

Claim 80 (original): The apparatus of Claim 38 wherein said bias power generator has a bias frequency between 100 kHz and 3 MHz.

Claim 81 (original): The apparatus of Claim 38 wherein said

bias power generator has a bias frequency of about 2 MHz to within about 5%.